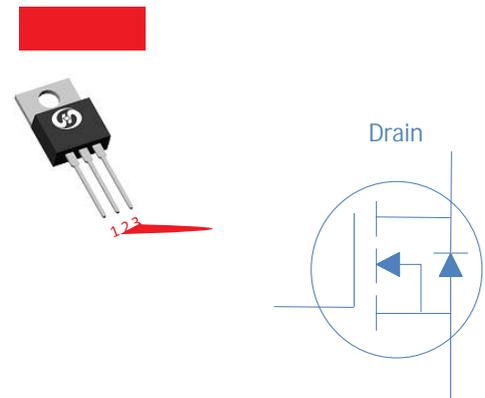




## 100V N-Ch Power MOSFET

$V_{DS}$		100	V
$R_{DS(on),typ}$	TO-263	3.4	m $\Omega$
$R_{DS(on),typ}$	TO-220	3.7	m $\Omega$
$I_D$		161	A



Part Number	Package	Marking
HGB042N10S	TO-263	GB042N10S
HGP042N10S	TO-220	GP042N10S

Absolute Maximum Ratings at  $T_J=25$  (unless otherwise specified)

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current	$I_D$	$T_C=25$	161	A
		$T_C=100$	114	
Drain to Source Voltage	$V_{DS}$	-	100	V
Gate to Source Voltage	$V_{GS}$	-	$\pm 20$	V
Pulsed Drain Current	$I_{DM}$	-	450	A
Avalanche Energy, Single Pulse	$E_{AS}$	$L=0.1\text{mH}, T_C=25$	180	mJ
Power Dissipation	$P_D$	$T_C=25$	214	W
Operating and Storage Temperature	$T_J, T_{stg}$	-	-55 to 175	

## Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Case	$R_{JC}$	0.7	$\text{W}/\text{W}$
Thermal Resistance Junction-Ambient	$R_{JA}$	60	$\text{W}/\text{W}$



Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	100	-	-
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	2	3	4
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS}=0V, V_{DS}=100V, T_j=100$	-	-	1
			-	-	100
			-	-	$\pm 100$
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$	-	3.7	4.2
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$	-	3.7	4.2
Transconductance	$g_{fs}$		70	-	-

Fig 1. Typical Output Characteristics

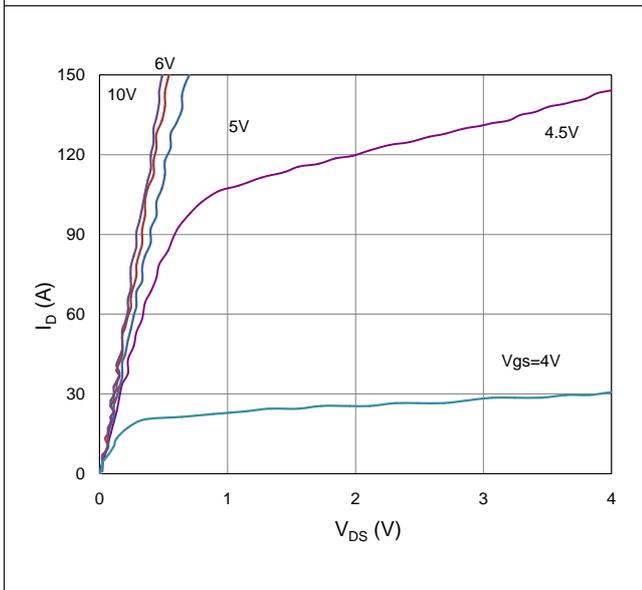


Figure 2. On-Resistance vs. Gate-Source Voltage

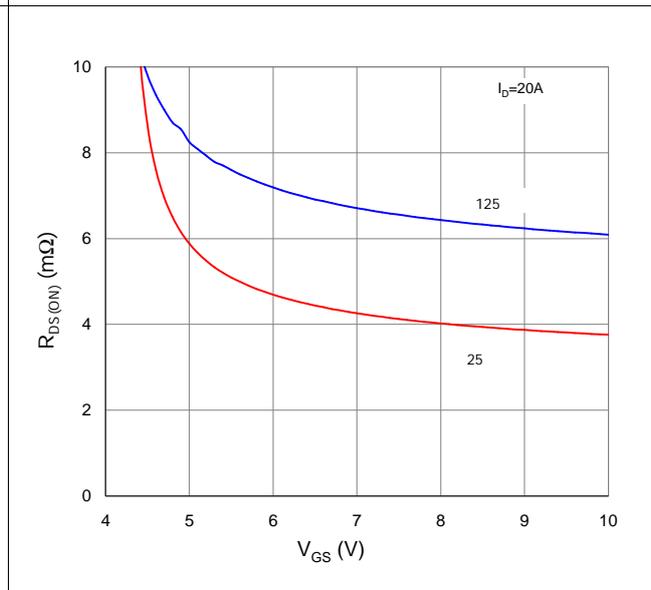


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

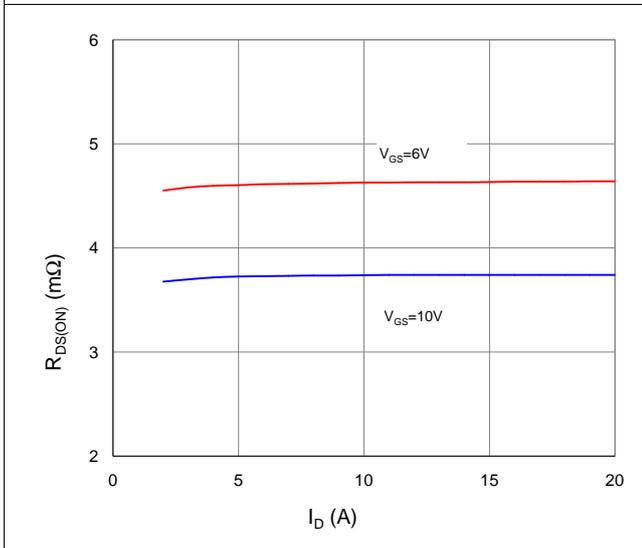


Figure 4. Normalized On-Resistance vs. Junction Temperature

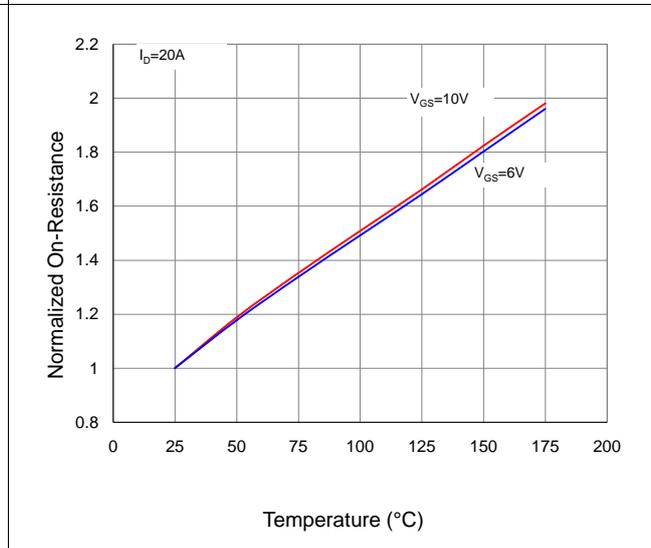


Figure 5. Typical Transfer Characteristics

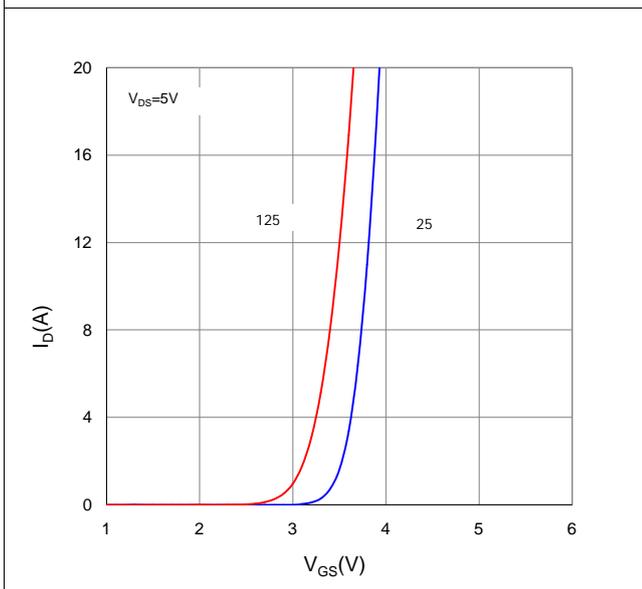
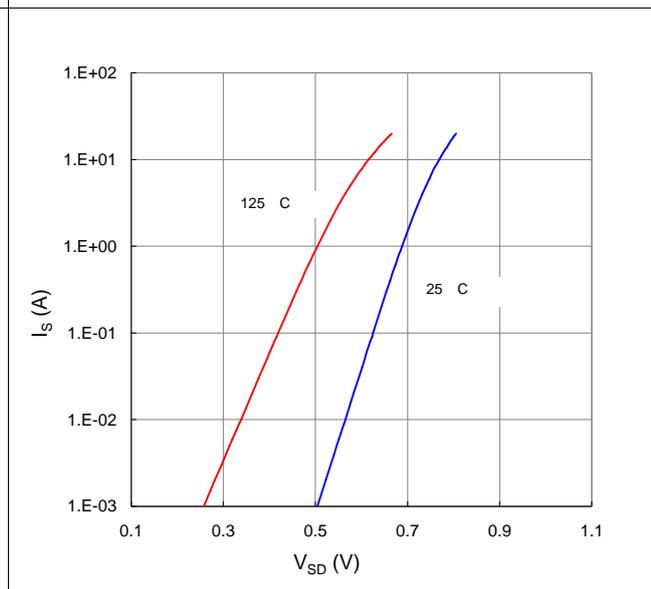
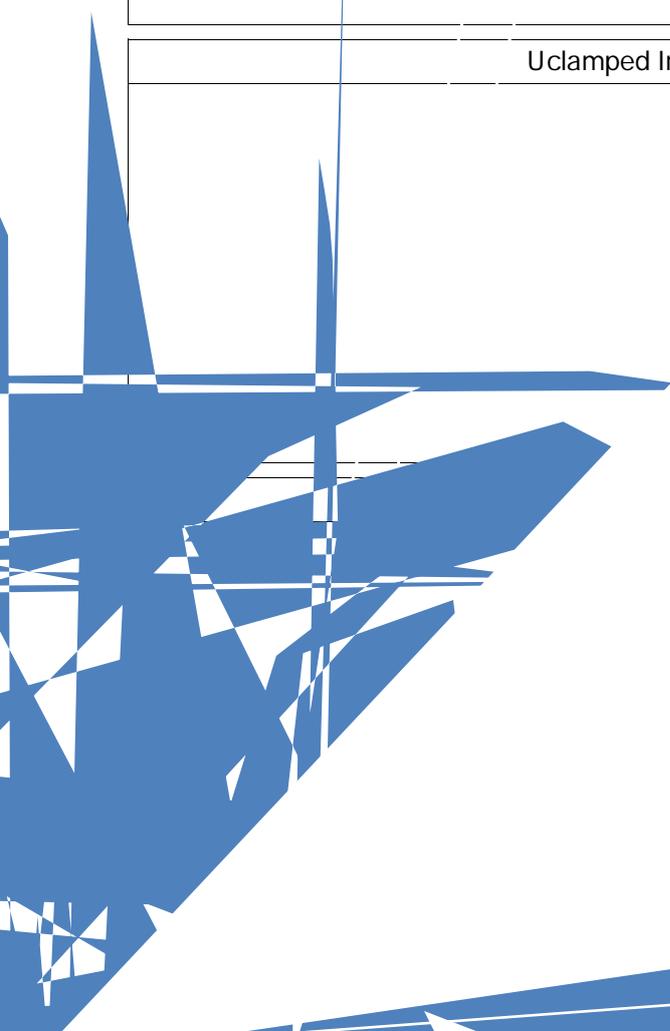


Figure 6. Typical Source-Drain Diode Forward Voltage





<p>Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage</p>	<p>Figure 8. Typical Capacitance vs. Drain-to-Source Voltage</p>
<p>Figure 9. Maximum Safe Operating Area</p>	<p>Figure 10. Maximun Drain Current vs. Case Temperature</p>
<p>Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Case</p>	

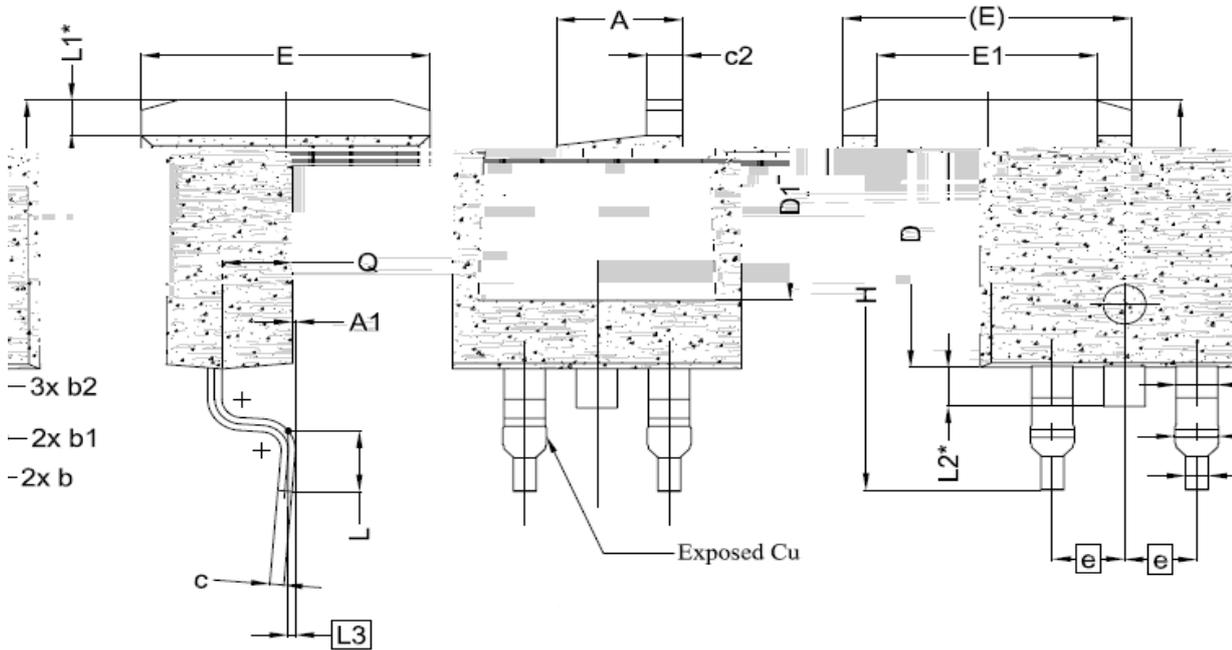


Uclamped Inductive

rest



TO-263, 3 leads



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.70	0.80	0.90
b1	1.20	1.55	1.75
b2	1.20	1.45	1.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	6.86	7.65	—
E	9.96	10.16	10.36
E1	6.89	7.77	7.89
e	2.54 BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.79
L1	1.36 REF.		
L2	1.50 REF.		
L3	0.25 BSC		
Q	2.30	2.48	2.70